

N-channel 60 V, 4.6 mΩ standard level MOSFET in TO220 Rev. 3 — 18 April 2012 Product data

Product data sheet

Product profile 1.

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1.1 General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	60	V
I _D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> -	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	211	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	-	8.05	10.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	3.5	4.6	mΩ
Dynamic	characteristics					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 30 V;	-	14.8	-	nC
Q _{G(tot)}	total gate charge	see Figure 14; see Figure 15	-	70.8	-	nC
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; \text{T}_{j(init)} = 25 \text{ °C}; \text{I}_{\text{D}} = 100 \text{ A}; \\ V_{sup} \leq 60 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \text{ unclamped} $	-	-	266	mJ

[1] Continuous current is limited by package.

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N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
3 mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R6-60PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

4. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN4R6-60PS	PSMN4R6-60PS

N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220

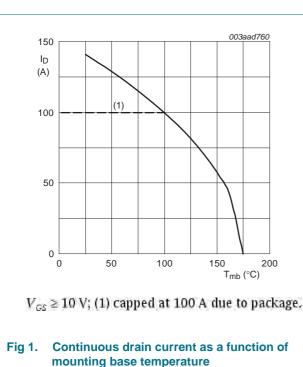
5. Limiting values

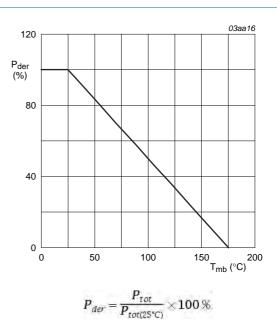
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V _{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	60	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u> _	99.7	А
		T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	100	А
I _{DM}	peak drain current	pulsed; t _p = 10 μs; T _{mb} = 25 °C; see <u>Figure 3</u>	-	565	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	211	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	in diode				
I _S	source current	T _{mb} = 25 °C	<u>[1]</u> -	100	А
I _{SM}	peak source current	pulsed; $t_p = 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$	-	565	А
Avalanche r	ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C}; I_{D} = 100 \text{ A}; $	-	266	mJ

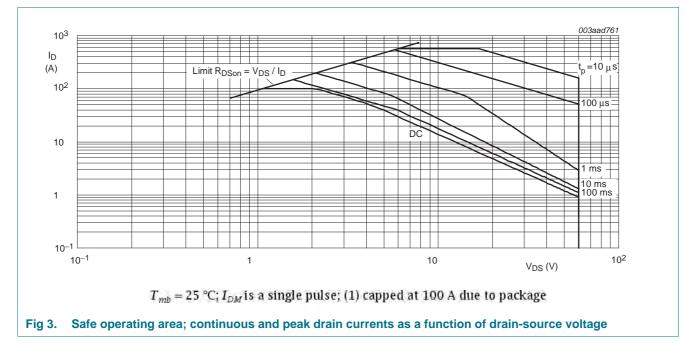
[1] Continuous current is limited by package.





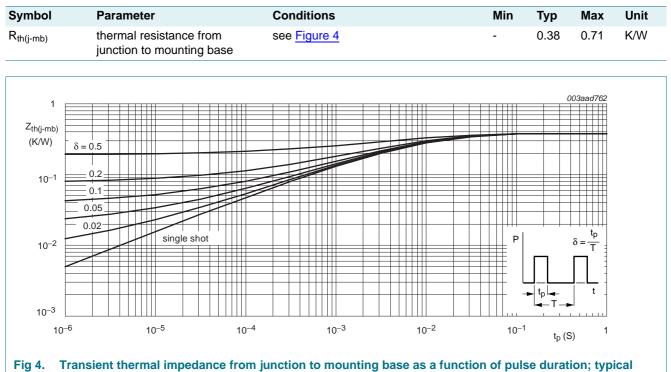
PSMN4R6-60PS

N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220



6. Thermal characteristics

Table 6.Thermal characteristics



values.

N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220

7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _{(BR)DSS}	drain-source	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	54	-	-	V
	breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V _{GSth}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 11</u>	-	-	4.6	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 11</u>	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C	-	-	200	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12</u>	-	8.05	10.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; see <u>Figure 12</u>	-	-	7.4	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	-	3.5	4.6	mΩ
R _G	gate resistance	f = 1 MHz	-	0.79	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	63	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 30 \text{ V}; V_{GS} = 10 \text{ V};$	-	70.8	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	19.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u>	-	13.5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6	-	nC
Q _{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 30 V; V_{GS} = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	14.8	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 30 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4426	-	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	567	-	pF
C _{rss}	reverse transfer capacitance		-	293	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 1.2 \Omega; V_{GS} = 10 \text{ V}; \label{eq:VDS}$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	58	-	ns
t _f	fall time		-	22	-	ns

PSMN4R6-60PS Product data sheet Symbol

PSMN4R6-60PS

Max

Unit

Тур

N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220

Min

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	ain diode		/ — — — —					• /
SD	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}$ see <u>Figure 17</u>	V; T _j = 25 °C;	-	C).81	1.1	V
	reverse recovery time		100 A/µs; V _{GS} = 0 V;	-	4	15	-	ns
r	recovered charge	V _{DS} = 30 V		-	6	64	-	nC
,100	15 6 5.5 5	003aad763	100				003aad769	
I _D (A)		<u></u>	9fs (S)			+		
80			80					
-								
60			60					
10		4.5						
40			40					
20		GS (V) = 4	20					
		35(V) = 4						
0			。 					
			0		~~~	80	10	0
0	0.5 1 1	1.5 _{VDS (V)} ²	0 2	0 40	60	00	I _D (A) 10	-
0		^{1.5} V _{DS} (V) ²					I _D (A) ¹⁰⁰	-
0	0 0.5 1 1 $T_j = 25 ^{\circ}C$	^{1.5} V _{DS} (V) ²		$T_j = 25 ^{\circ}\mathrm{C};$			I _D (A)	-
					$V_{DS} = 1$	10 V		
-ig 5. O	$T_j = 25 \circ C$	n current as a	Fig 6. Forward	$T_j = 25 ^{\circ}\mathrm{C};$	$V_{DS} = 1$	10 V e as a		
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
[∓] ig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a	Fig 6. Forward drain cur	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es		
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur ⁸⁰⁰⁰ C	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF)	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur ⁸⁰⁰⁰ C	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF)	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$ sutput characteristics: drain	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF)	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 ^{\circ}C$	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 \text{ °C}$ rutput characteristics: drain inction of drain-source volt $T_j = 175 \text{ °C}$	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000 4000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu	$T_j = 25 \text{ °C}$ rutput characteristics: drain inction of drain-source volt $T_j = 175 \text{ °C}$	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu ¹⁰⁰ (A) 80 60 40	$T_j = 25 \text{ °C}$ rutput characteristics: drain inction of drain-source volt $T_j = 175 \text{ °C}$	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000 4000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu ¹⁰⁰ (A) 80 60 40	$T_j = 25 \text{ °C}$ rutput characteristics: drain inction of drain-source volt $T_j = 175 \text{ °C}$	n current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000 4000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es	functio	
Fig 5. O fu ¹⁰⁰ (A) 80 60 40	$T_j = 25 ^{\circ}C$ putput characteristics: drain inction of drain-source volt $T_j = 175 ^{\circ}C$	h current as a tage; typical values	Fig 6. Forward drain cur 8000 C (pF) 6000 4000	$T_j = 25$ °C; transcond	$V_{DS} = 1$	10 V e as a es o	Crss	on of
Fig 5. O fu	$T_j = 25 \text{ °C}$	003aad765	Fig 6. Forward drain cur	T _j = 25 °C; transcond rrent; typic	V _{DS} = 1		functio	on of
Fig 5. O fu	$T_j = 25 ^{\circ}C$ Putput characteristics: drain Inction of drain-source volt T_j = 175 ^{\circ}C	h current as a tage; typical values	Fig 6. Forward drain cur	T _j = 25 °C; transcond rrent; typic	V _{DS} = 1		Crss	on of
Fig 5. O fu	$T_j = 25 \text{ °C}$	$\frac{003aad765}{T_j = 25 \circ C}$	Fig 6. Forward drain cur	T _j = 25 °C; transcond rrent; typic	$V_{DS} = 1$ uctance al value $V_{DS} = 0$	10 V e as a o o VG: 0 V	functio	on of

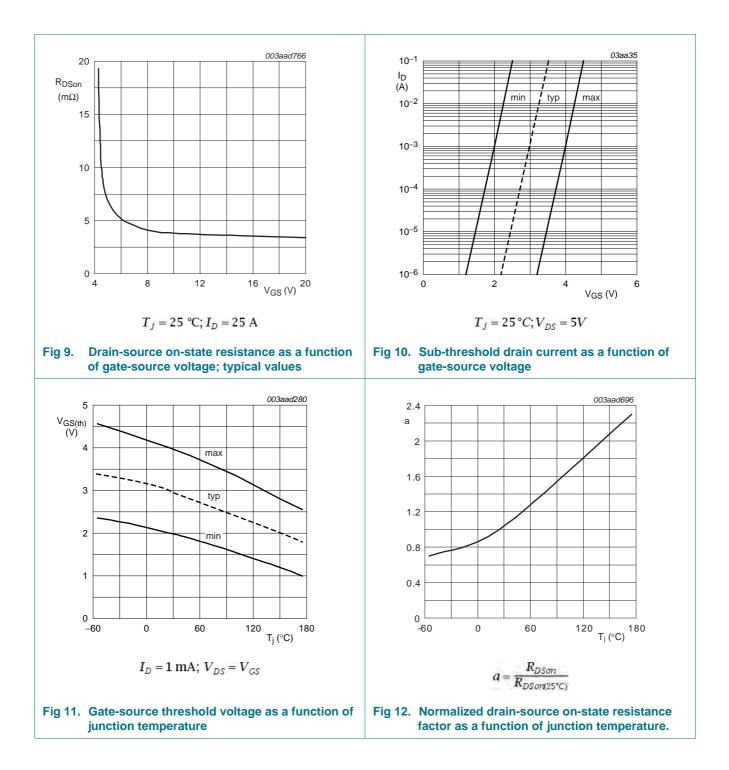
Table 7. Characteristics ...continued

Parameter

Conditions

PSMN4R6-60PS

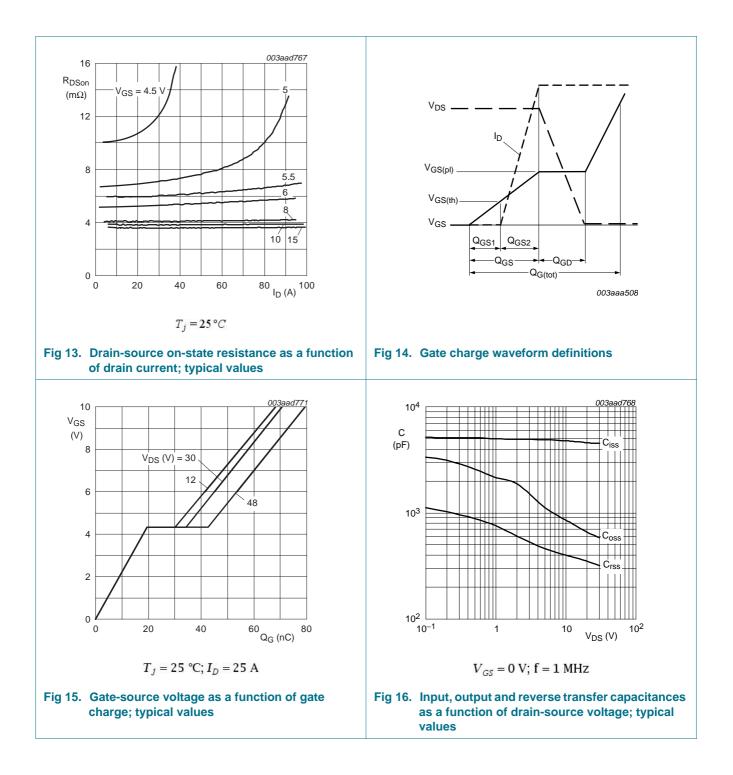
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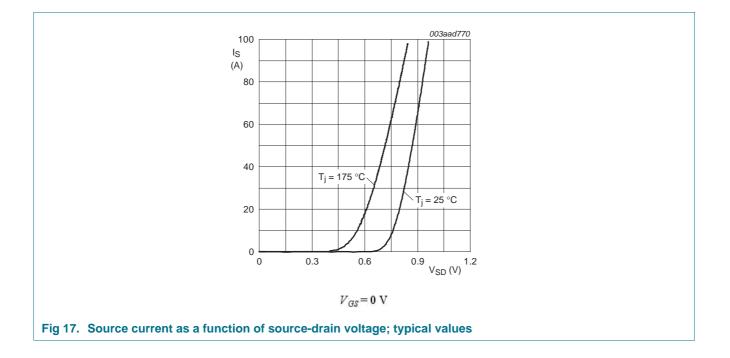
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Package outline 8.

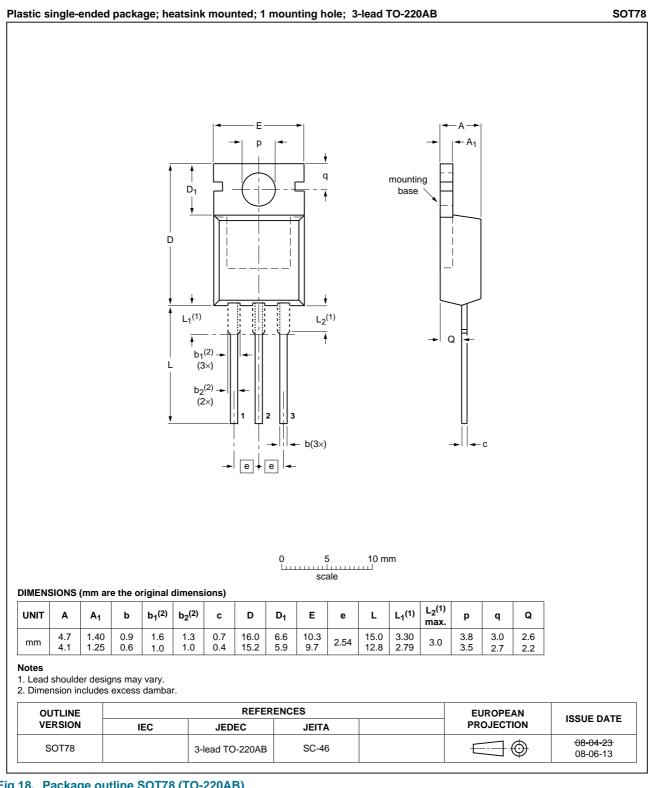


Fig 18. Package outline SOT78 (TO-220AB)

PSMN4R6-60PS **Product data sheet**

N-channel 60 V, 4.6 m Ω standard level MOSFET in TO220

9. Revision history

Table 8.	Revision history	
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Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R6-60PS v.3	20120418	Product data sheet	-	PSMN4R6-60PS v.2
Modifications:	 Various changes t 	o content.		
PSMN4R6-60PS v.2	20101101	Product data sheet	-	PSMN4R6-60PS v.1

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Product data sheet

PSMN4R6-60PS

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N-channel 60 V, 4.6 mΩ standard level MOSFET in TO220

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